

Muhammad M A Mirza

List of Publications by Year in descending order

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Version: 2024-02-01

15

papers

624

citations

1163117

8

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1474206

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docs citations

15

times ranked

1074

citing authors

#	ARTICLE	IF	CITATIONS
1	THz intersubband electroluminescence from n-type Ge/SiGe quantum cascade structures. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	15
2	Terahertz intersubband electroluminescence from n-type germanium quantum wells. , 2021, , .		0
3	THz Intersubband Emitter based on Silicon. , 2021, , .		0
4	3D LIDAR imaging using Ge-on-Si single-photon avalanche diode detectors. <i>Optics Express</i> , 2020, 28, 1330.	3.4	45
5	Ge-on-Si Single Photon Avalanche Diode Detectors for LIDAR in the Short Wave Infrared. , 2020, , .		1
6	High performance planar germanium-on-silicon single-photon avalanche diode detectors. <i>Nature Communications</i> , 2019, 10, 1086.	12.8	104
7	Geiger Mode Ge-on-Si Single-Photon Avalanche Diode Detectors. , 2019, , .		2
8	Geiger Mode Ge-on-Si Single-Photon Avalanche Diode Detectors. , 2019, , .		3
9	Quantum interference in silicon one-dimensional junctionless nanowire field-effect transistors. <i>Physical Review B</i> , 2018, 98, .	3.2	5
10	Experimental and Simulation Study of Silicon Nanowire Transistors Using Heavily Doped Channels. <i>IEEE Nanotechnology Magazine</i> , 2017, 16, 727-735.	2.0	17
11	One dimensional transport in silicon nanowire junction-less field effect transistors. <i>Scientific Reports</i> , 2017, 7, 3004.	3.3	31
12	Variability study of high current junctionless silicon nanowire transistors. , 2017, , .		2
13	Design and fabrication of memory devices based on nanoscale polyoxometalate clusters. <i>Nature</i> , 2014, 515, 545-549.	27.8	301
14	Determining the Electronic Performance Limitations in Top-Down-Fabricated Si Nanowires with Mean Widths Down to 4 nm. <i>Nano Letters</i> , 2014, 14, 6056-6060.	9.1	25
15	Nanofabrication of high aspect ratio ($\sqrt[4]{50}:1$) sub-10nm silicon nanowires using inductively coupled plasma etching. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012, 30, .	1.2	73